

High Speed, High Gain Bipolar NPN Power Transistor

with Integrated Collector-Emitter
Diode and Built-in Efficient
Antisaturation Network

BUL45D2G

The BUL45D2G is state-of-art High Speed High gain BiPolar transistor (H2BIP). High dynamic characteristics and lot-to-lot minimum spread (± 150 ns on storage time) make it ideally suitable for light ballast applications. Therefore, there is no need to guarantee an h_{FE} window. It's characteristics make it also suitable for PFC application.

Features

- Low Base Drive Requirement
- High Peak DC Current Gain
- Extremely Low Storage Time Min/Max Guarantees Due to the H2BIP Structure which Minimizes the Spread
- Integrated Collector-Emitter Free Wheeling Diode
- Fully Characterized and Guaranteed Dynamic $V_{CE(sat)}$
- "6 Sigma" Process Providing Tight and Reproducible Parameter Spreads
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

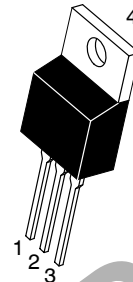
Symbo l	Rating	Value	Unit
V_{CEO}	Collector-Emitter Sustaining Voltage	400	Vdc
V_{CBO}	Collector-Base Breakdown Voltage	700	Vdc
V_{CES}	Collector-Emitter Breakdown Voltage	700	Vdc
V_{EBO}	Emitter-Base Voltage	12	Vdc
I_C	Collector Current – Continuous	5	Adc
I_{CM}	Collector Current – Peak (Note 1)	10	Adc
I_B	Base Current – Continuous	2	Adc
I_{BM}	Base Current – Peak (Note 1)	4	Adc
P_D	Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	75 0.6	W W/ $^\circ\text{C}$
T_J, T_{stg}	Operating and Storage Temperature	-65 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

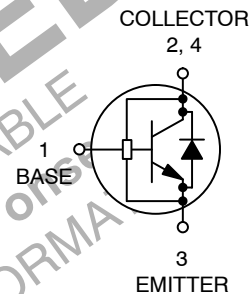
1. Pulse Test: Pulse Width = 5 ms, Duty Cycle $\leq 10\%$.

* For additional information on our Pb-Free strategy and soldering details, please download the [onsemi Soldering and Mounting Techniques Reference Manual](#), [SOLDERRM/D](#).

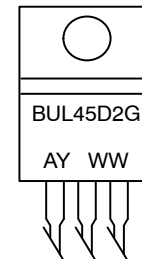
POWER TRANSISTOR
5.0 AMPERES,
700 VOLTS, 75 WATTS



TO-220-3
CASE 221A
STYLE 1



MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
BUL45D2G	TO-220-3 (Pb-Free)	50 Units / Rail

BUL45D2G

THERMAL CHARACTERISTICS

Symbol	Characteristics	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.65	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^{\circ}\text{C}/\text{W}$
T_L	Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 5 Seconds	260	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

$V_{CE(sus)}$	Collector-Emitter Sustaining Voltage ($I_C = 100\text{ mA}$, $L = 25\text{ mH}$)	400	450	–	Vdc
V_{CBO}	Collector-Base Breakdown Voltage ($I_{CBO} = 1\text{ mA}$)	700	910	–	Vdc
V_{EBO}	Emitter-Base Breakdown Voltage ($I_{EBO} = 1\text{ mA}$)	12	14.1	–	Vdc
I_{CEO}	Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CE0}$, $I_B = 0$)	–	–	100	μAdc
I_{CES}	Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CES}$, $V_{EB} = 0$) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ($V_{CE} = 500\text{ V}$, $V_{EB} = 0$) @ $T_C = 125^{\circ}\text{C}$	– – –	– – –	100 500 100	μAdc
I_{EBO}	Emitter-Cutoff Current ($V_{EB} = 10\text{ Vdc}$, $I_C = 0$)	–	–	100	μAdc

ON CHARACTERISTICS

$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C = 0.8\text{ Adc}$, $I_B = 80\text{ mAdc}$) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ($I_C = 2\text{ Adc}$, $I_B = 0.4\text{ Adc}$) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$	– – – –	0.8 0.7 0.89 0.79	1 0.9 1 0.9	Vdc
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C = 0.8\text{ Adc}$, $I_B = 80\text{ mAdc}$) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ($I_C = 2\text{ Adc}$, $I_B = 0.4\text{ Adc}$) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ($I_C = 0.8\text{ Adc}$, $I_B = 40\text{ mAdc}$) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$	– – – – – –	0.28 0.32 0.32 0.38 0.46 0.62	0.4 0.5 0.5 0.6 0.75 1	Vdc
h_{FE}	DC Current Gain ($I_C = 0.8\text{ Adc}$, $V_{CE} = 1\text{ Vdc}$) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ($I_C = 2\text{ Adc}$, $V_{CE} = 1\text{ Vdc}$) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$	22 20 10 7	34 29 14 9.5	– – – –	–

DIODE CHARACTERISTICS

V_{EC}	Forward Diode Voltage ($I_{EC} = 1\text{ Adc}$) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ($I_{EC} = 2\text{ Adc}$) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ($I_{EC} = 0.4\text{ Adc}$) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$	– – – – – –	1.04 0.7 1.2 – 0.85 0.62	1.5 – 1.6 – 1.2 –	V
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BUL45D2G

ELECTRICAL CHARACTERISTICS (T_C = 25 °C unless otherwise noted) (continued)

Symbol	Characteristic	Min	Typ	Max	Unit
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DIODE CHARACTERISTICS

T _{fr}	Forward Recovery Time (see Figure 27)				ns
	(I _F = 1 Adc, di/dt = 10 A/μs)				
	@ T _C = 25 °C	–	330	–	
	(I _F = 2 Adc, di/dt = 10 A/μs)				
	@ T _C = 25 °C	–	360	–	
	(I _F = 0.4 Adc, di/dt = 10 A/μs)				
	@ T _C = 25 °C	–	320	–	

DYNAMIC CHARACTERISTICS

f _T	Current Gain Bandwidth (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1 MHz)	–	13	–	MHz
C _{ob}	Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1 MHz)	–	50	75	pF
C _{ib}	Input Capacitance (V _{EB} = 8 Vdc)	–	340	500	pF

DYNAMIC SATURATION VOLTAGE

V _{CE(dsat)}	Dynamic Saturation Voltage: Determined 1 μs and 3 μs respectively after rising I _{B1} reaches 90% of final I _{B1}	I _C = 1 A I _{B1} = 100 mA V _{CC} = 300 V	@ 1 μs	@ T _C = 25°C @ T _C = 125°C	– –	3.7 9.4	– –	V
			@ 3 μs	@ T _C = 25°C @ T _C = 125°C	– –	0.35 2.7	– –	V
		I _C = 2 A I _{B1} = 0.8 A V _{CC} = 300 V	@ 1 μs	@ T _C = 25°C @ T _C = 125°C	– –	3.9 12	– –	V
			@ 3 μs	@ T _C = 25°C @ T _C = 125°C	– –	0.4 1.5	– –	V

SWITCHING CHARACTERISTICS: Resistive Load (D.C. ≤ 10%, Pulse Width = 20 μs)

t _{on}	Turn-on Time	I _C = 2 Adc, I _{B1} = 0.4 Adc I _{B2} = 1 Adc V _{CC} = 300 Vdc	@ T _C = 25°C @ T _C = 125°C	– –	90 105	150 –	ns
t _{off}	Turn-off Time		@ T _C = 25°C @ T _C = 125°C	– –	1.15 1.5	1.3 –	μs
t _{on}	Turn-on Time	I _C = 2 Adc, I _{B1} = 0.4 Adc I _{B2} = 0.4 Adc V _{CC} = 300 Vdc	@ T _C = 25°C @ T _C = 125°C	– –	90 110	150 –	ns
t _{off}	Turn-off Time		@ T _C = 25°C @ T _C = 125°C	2.1 –	– 3.1	2.4 –	μs

SWITCHING CHARACTERISTICS: Inductive Load (V_{clamp} = 300 V, V_{CC} = 15 V, L = 200 μH)

t _f	Fall Time	I _C = 1 Adc I _{B1} = 100 mA I _{B2} = 500 mA	@ T _C = 25°C @ T _C = 125°C	– –	90 93	150 –	ns
t _s	Storage Time		@ T _C = 25°C @ T _C = 125°C	– –	0.72 1.05	0.9 –	μs
t _c	Crossover Time		@ T _C = 25°C @ T _C = 125°C	– –	95 95	150 –	ns
t _f	Fall Time	I _C = 2 Adc I _{B1} = 0.4 Adc I _{B2} = 0.4 Adc	@ T _C = 25°C @ T _C = 125°C	– –	80 105	150 –	ns
t _s	Storage Time		@ T _C = 25°C @ T _C = 125°C	1.95 –	– 2.9	2.25 –	μs
t _c	Crossover Time		@ T _C = 25°C @ T _C = 125°C	– –	225 450	300 –	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL STATIC CHARACTERISTICS

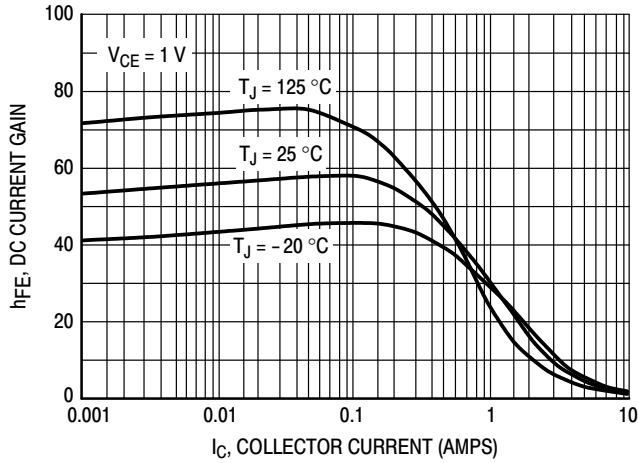


Figure 1. DC Current Gain @ 1 Volt

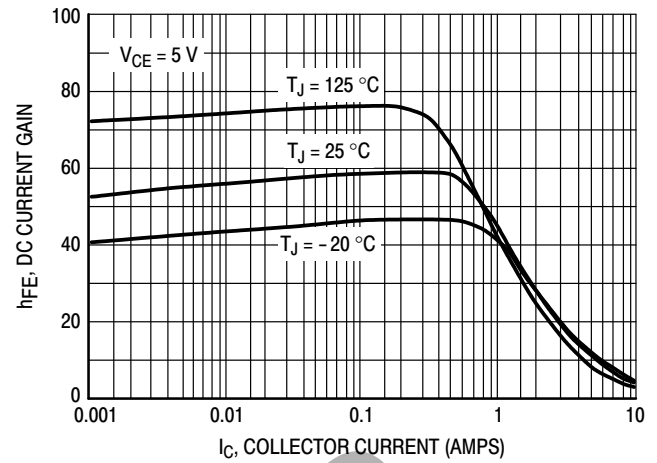


Figure 2. DC Current Gain @ 5 Volt

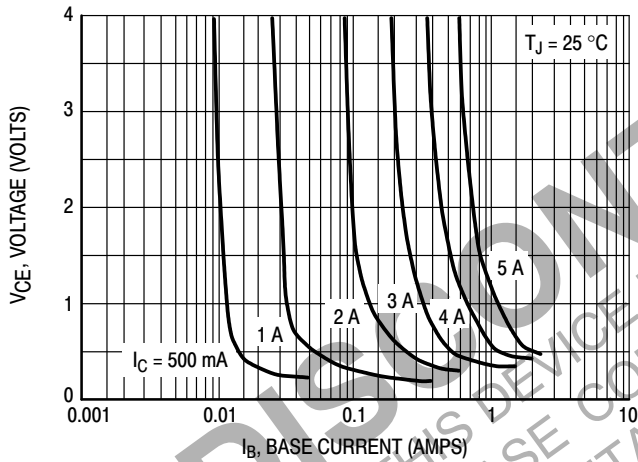


Figure 3. Collector Saturation Region

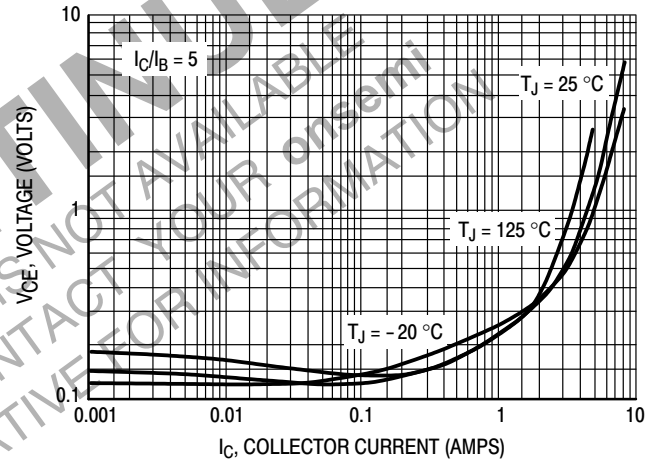


Figure 4. Collector-Emitter Saturation Voltage

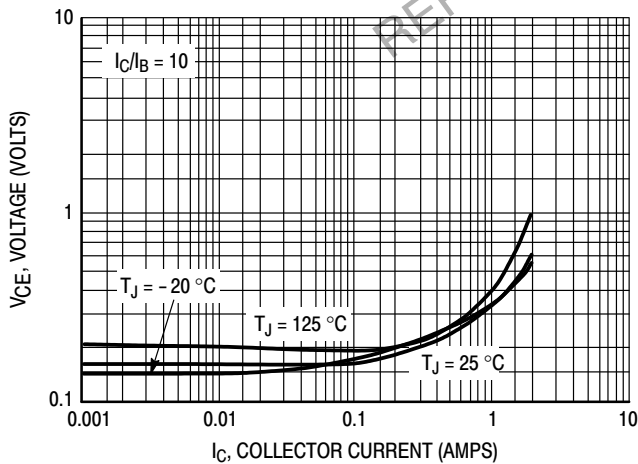


Figure 5. Collector-Emitter Saturation Voltage

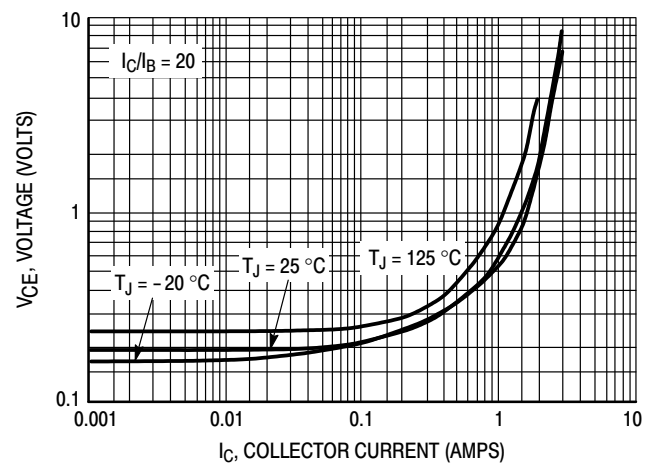


Figure 6. Collector-Emitter Saturation Voltage

TYPICAL STATIC CHARACTERISTICS (continue)

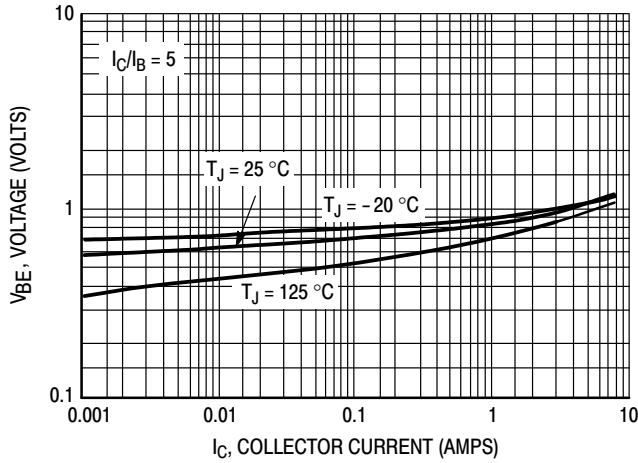


Figure 7. Base-Emitter Saturation Region

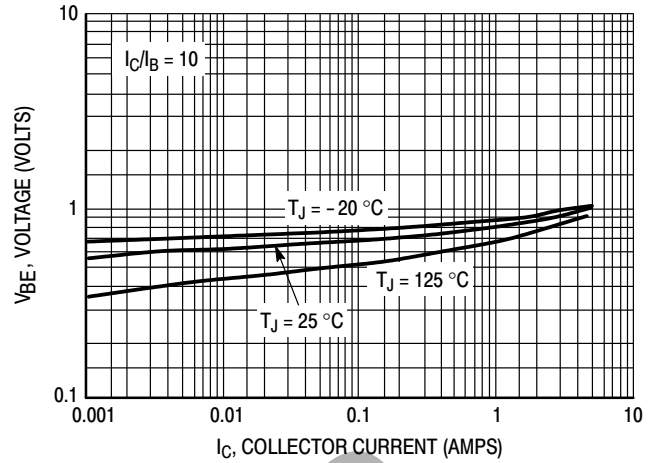


Figure 8. Base-Emitter Saturation Region

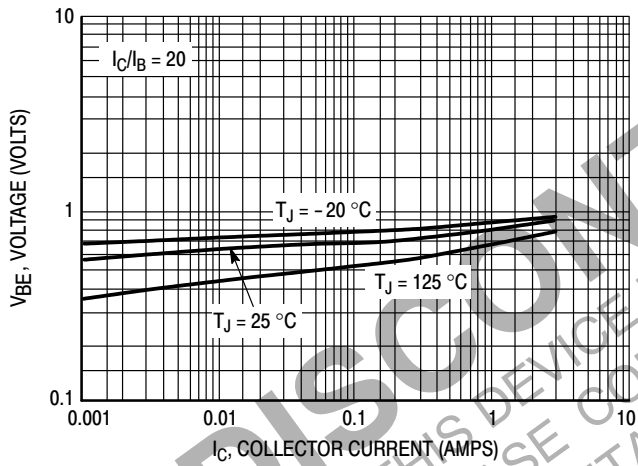


Figure 9. Base-Emitter Saturation Region

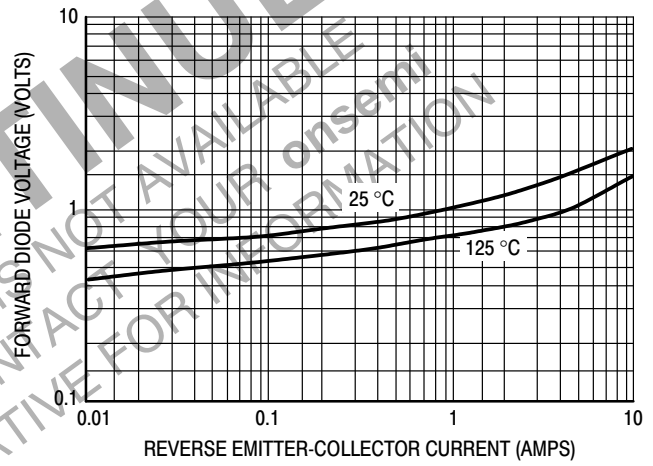


Figure 10. Forward Diode Voltage

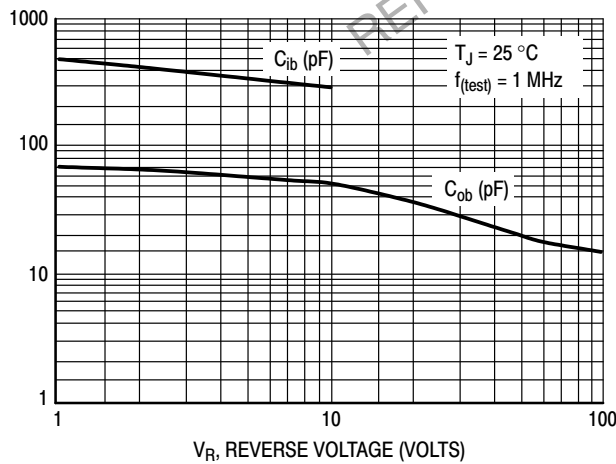


Figure 11. Capacitance

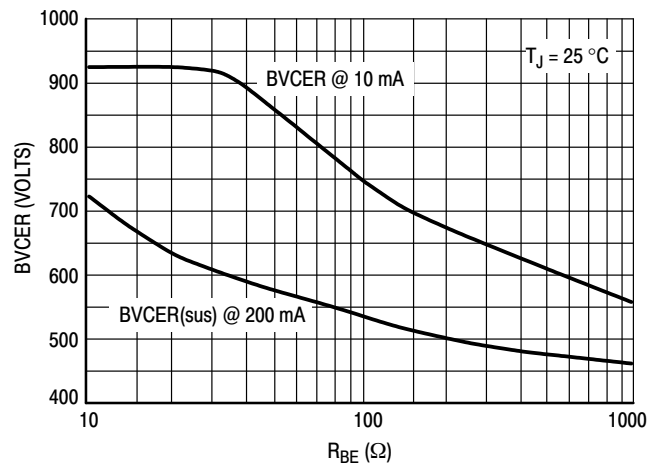


Figure 12. BVCER = f(I_CER)

TYPICAL SWITCHING CHARACTERISTICS

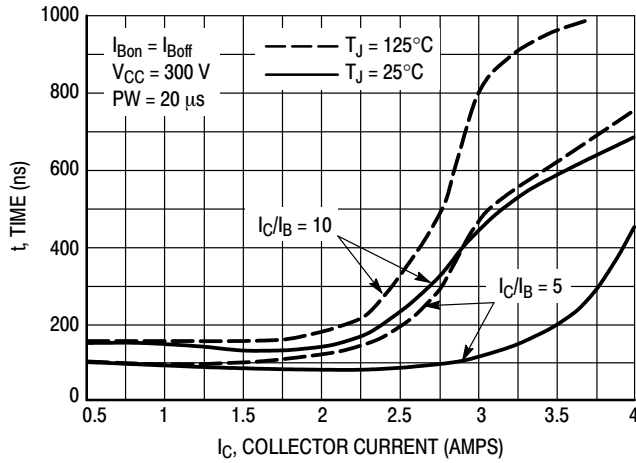


Figure 13. Resistive Switch Time, t_{on}

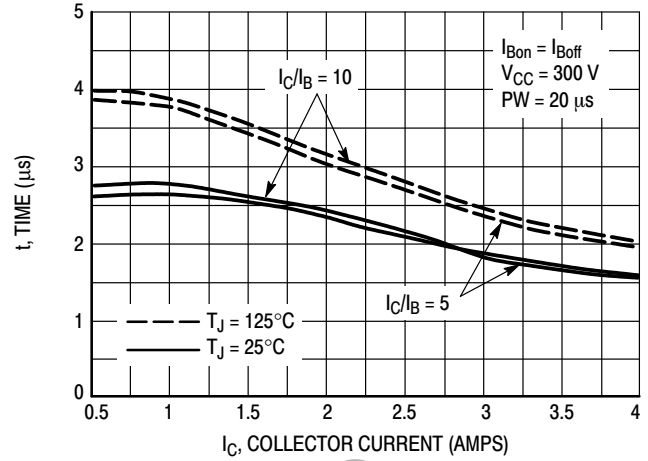


Figure 14. Resistive Switch Time, t_{off}

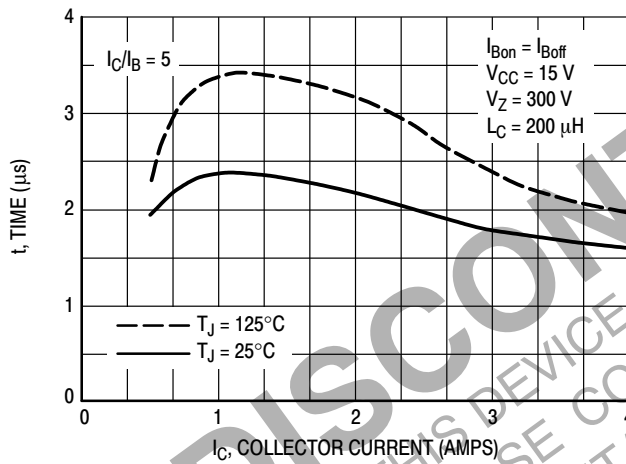


Figure 15. Inductive Storage Time,
 t_{si} @ $I_C/I_B = 5$

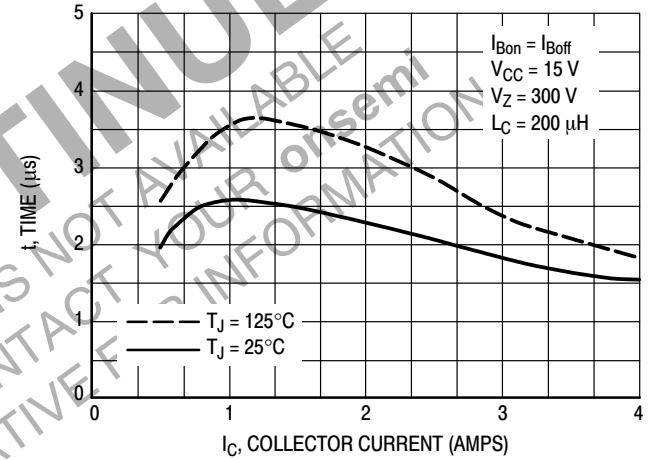


Figure 16. Inductive Storage Time,
 t_{si} @ $I_C/I_B = 10$

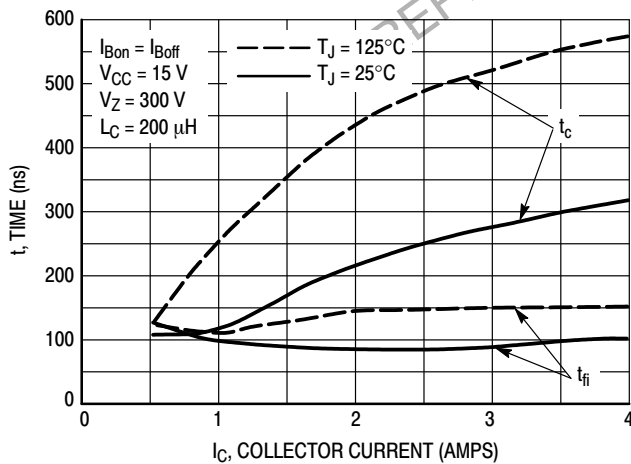


Figure 17. Inductive Switching,
 t_c & t_{fi} @ $I_C/I_B = 5$

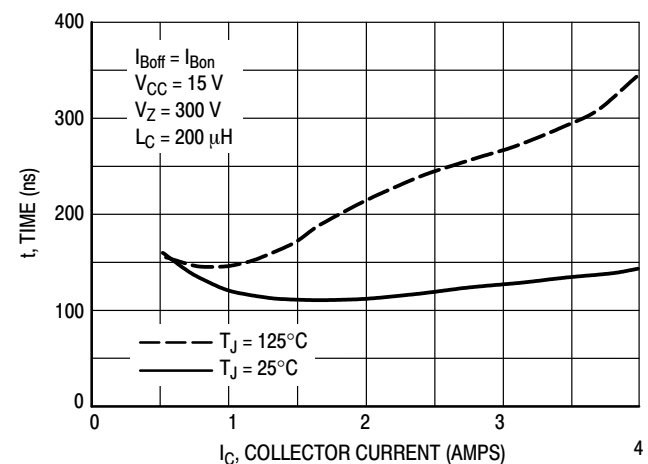


Figure 18. Inductive Switching,
 t_{fi} @ $I_C/I_B = 10$

TYPICAL SWITCHING CHARACTERISTICS (continue)

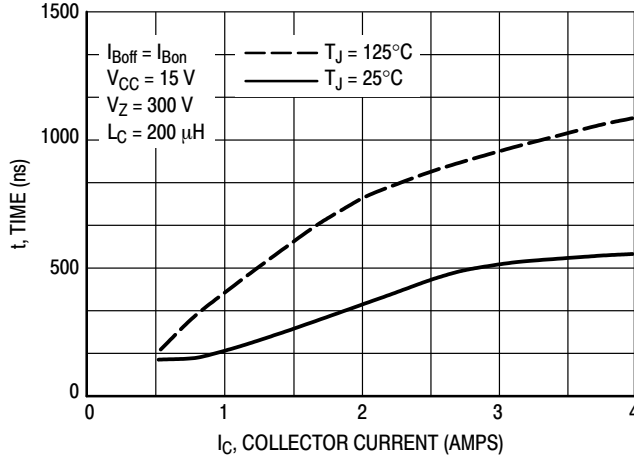


Figure 19. Inductive Switching, t_c @ $I_C/I_B = 10$

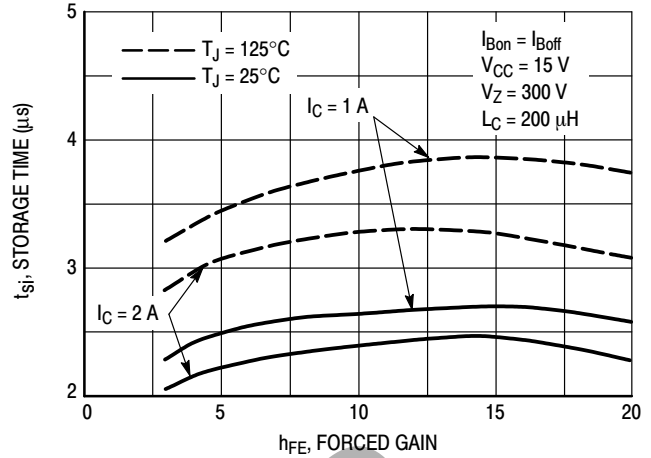


Figure 20. Inductive Storage Time

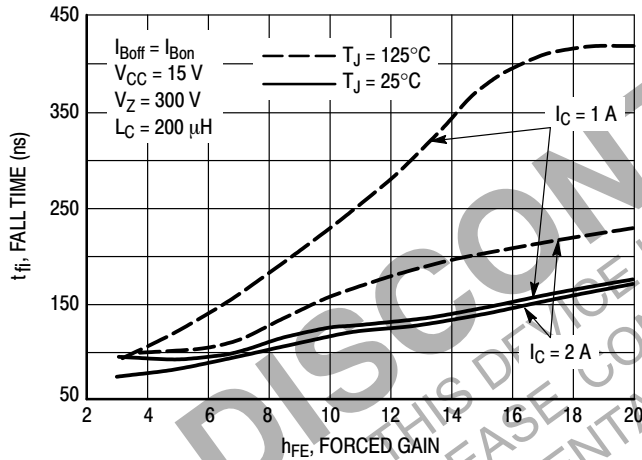


Figure 21. Inductive Fall Time

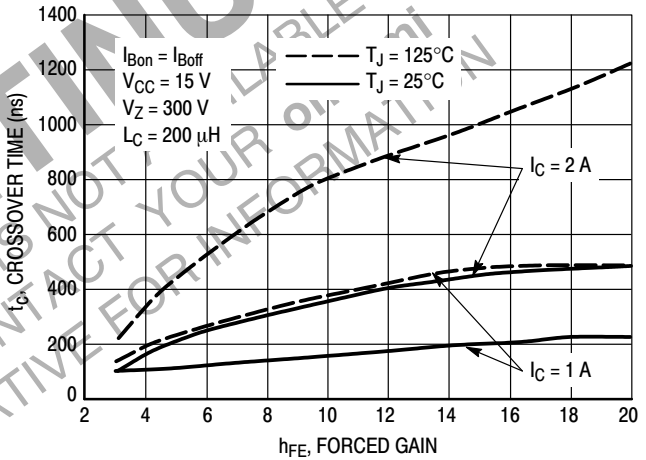


Figure 22. Inductive Crossover Time

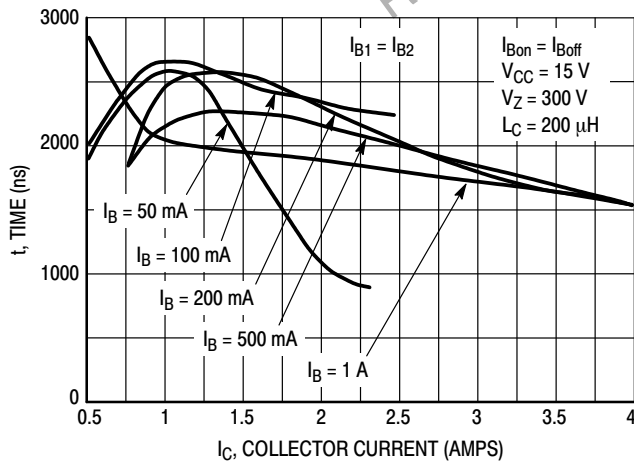


Figure 23. Inductive Storage Time, t_{si}

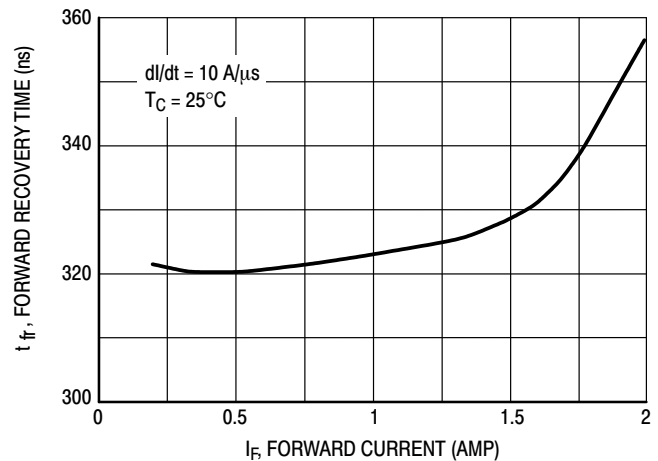


Figure 24. Forward Recovery Time t_{fr}

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TYPICAL SWITCHING CHARACTERISTICS (continue)

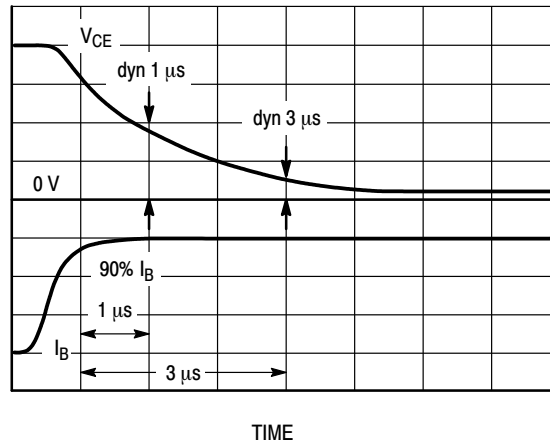


Figure 25. Dynamic Saturation Voltage Measurements

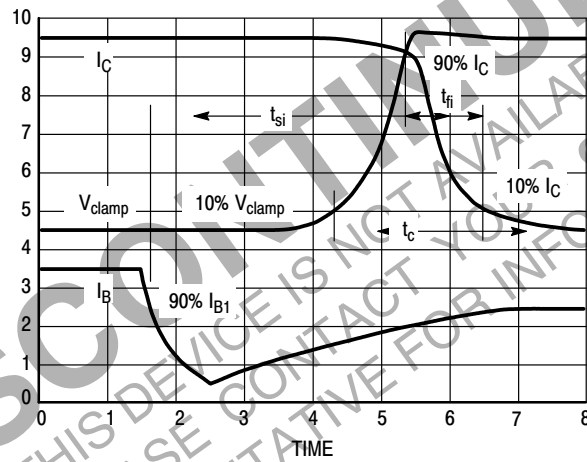


Figure 26. Inductive Switching Measurements

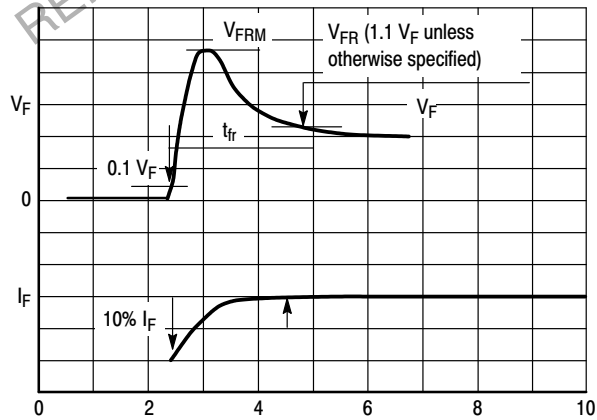
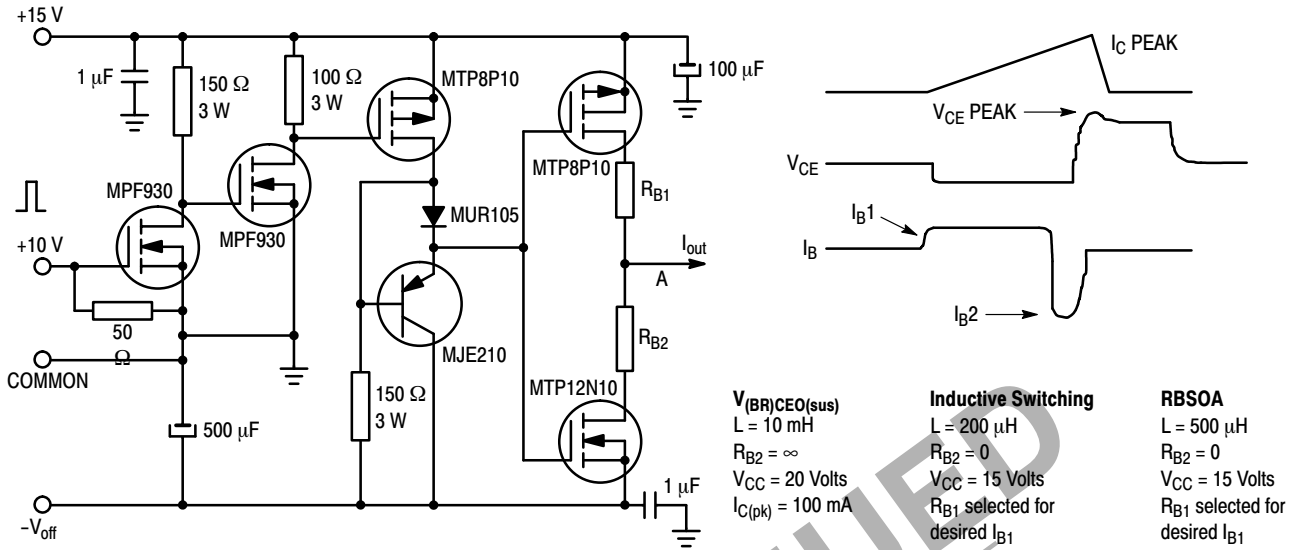


Figure 27. t_{fr} Measurements

BUL45D2G

TYPICAL SWITCHING CHARACTERISTICS (continue)

Table 1. Inductive Load Switching Drive Circuit



TYPICAL CHARACTERISTICS

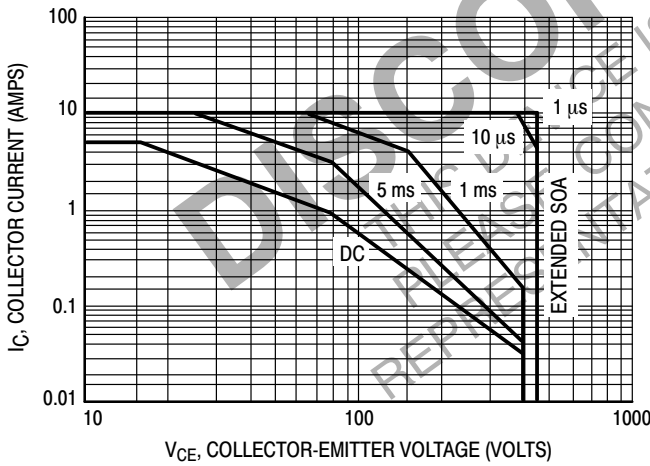


Figure 28. Forward Bias Safe Operating Area

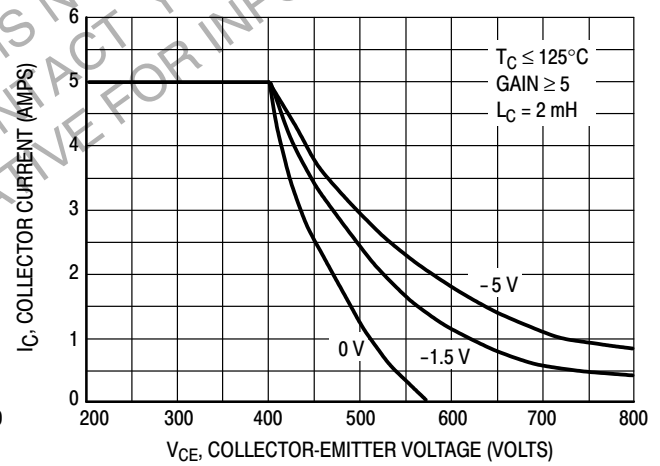


Figure 29. Reverse Bias Safe Operating Area

TYPICAL CHARACTERISTICS (continue)

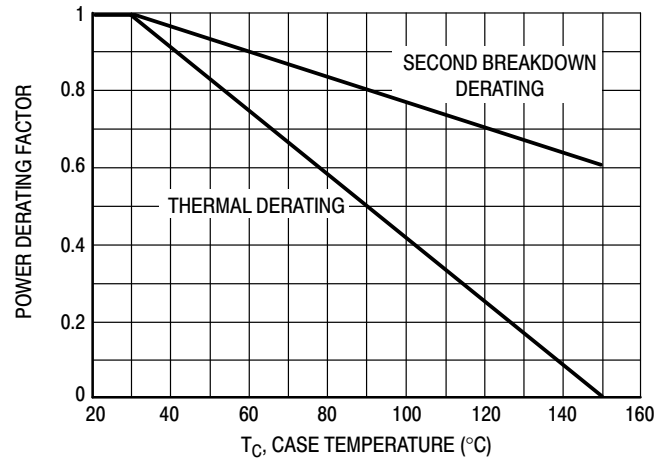


Figure 30. Forward Bias Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 28 is based on $T_C = 25^\circ\text{C}$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C > 25^\circ\text{C}$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on

Figure 28 may be found at any case temperature by using the appropriate curve on Figure 30.

$T_{J(pk)}$ may be calculated from the data in Figure 31. At any case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn-off with the base to emitter junction reverse biased. The safe level is specified as a reverse biased safe operating area (Figure 29). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.

TYPICAL THERMAL RESPONSE

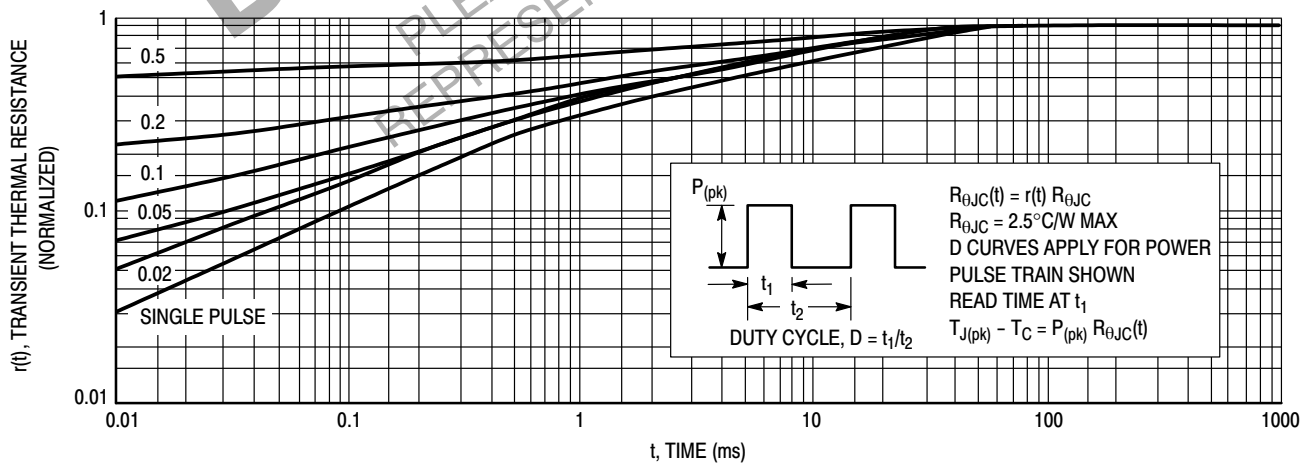


Figure 31. Typical Thermal Response ($Z_{thJC}(t)$) for BUL45D2

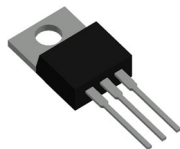
BUL45D2G

REVISION HISTORY

Revision	Description of Changes	Date
10	Data Sheet Discontinued.	1/14/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

DISCONTINUED
THIS DEVICE IS NOT AVAILABLE
PLEASE CONTACT YOUR onsemi
REPRESENTATIVE FOR INFORMATION

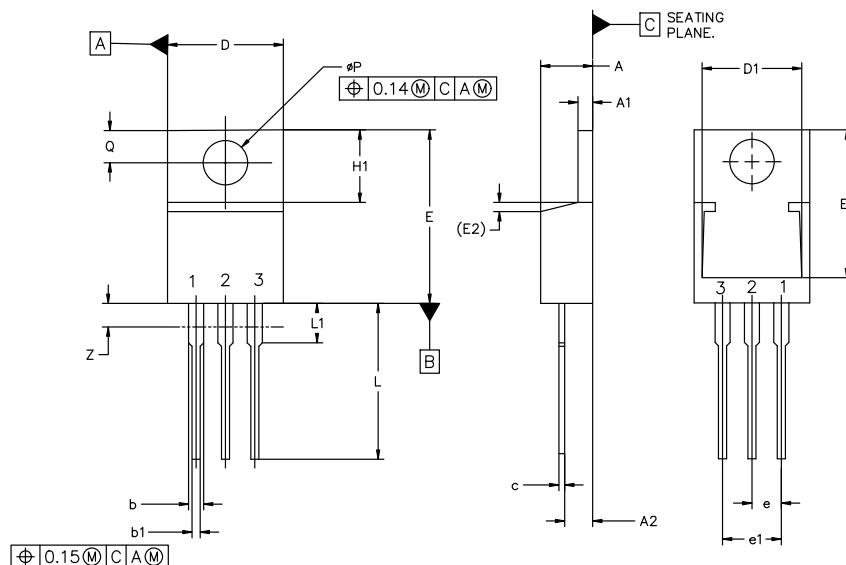


TO-220-3 10.10x15.12x4.45, 2.54P

CASE 221A

ISSUE AL

DATE 05 FEB 2025



MILLIMETERS			
DIM	MIN	NOM	MAX
A	4.07	4.45	4.83
A1	1.15	1.28	1.41
A2	2.04	2.42	2.79
b	1.15	1.34	1.52
b1	0.64	0.80	0.96
c	0.36	0.49	0.61
D	9.66	10.10	10.53
D1	8.43	8.63	8.83
E	14.48	15.12	15.75
E1	12.58	12.78	12.98
E2	1.27 REF		

MILLIMETERS			
DIM	MIN	NOM	MAX
e	2.42	2.54	2.66
e1	4.83	5.08	5.33
H1	5.97	6.22	6.47
L	12.70	13.49	14.27
L1	2.80	3.45	4.10
Q	2.54	2.79	3.04
øP	3.60	3.85	4.09
Z	---	---	3.48

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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